IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

KOCHERGIN ET AL.

Serial No. 10/686,519

Filed: 16 October 2003

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Atty. Ref.: 340-81

TC/A.U.: 2872

Examiner:

For: METHOD OF MANUFACTURING A SPECTRAL FILTER FOR

GREEN AND LONGER WAVELENGTHS

July 15, 2004

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

In accordance with Rule 97, the undersigned attorney submits the documents listed on the attached form PTO-1449. A copy of each document is enclosed.

The Examiner is requested to initial the attached form PTO-1449 and to return a copy to the undersigned as an indication that the listed documents have been considered and made of record in this case.

Respectfully submitted,

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Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.

*Examiner

Date Considered